



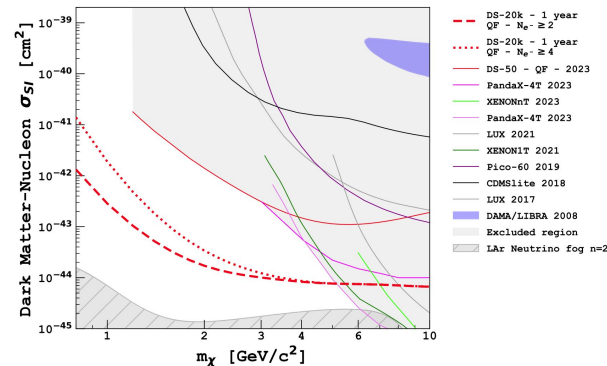
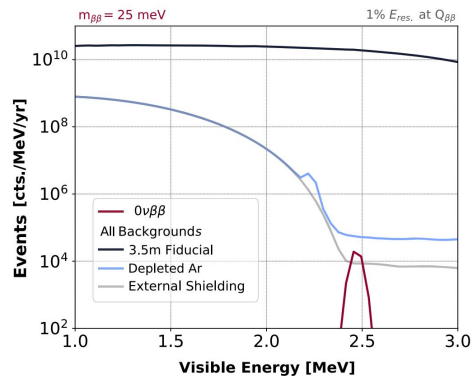
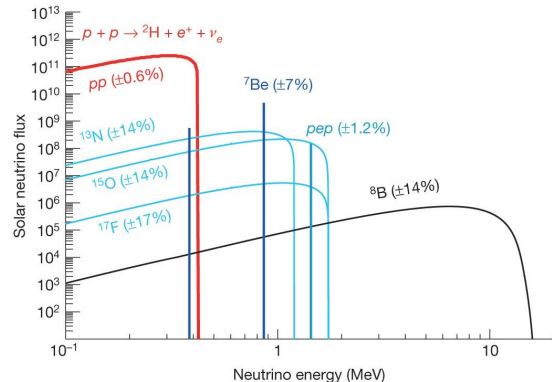
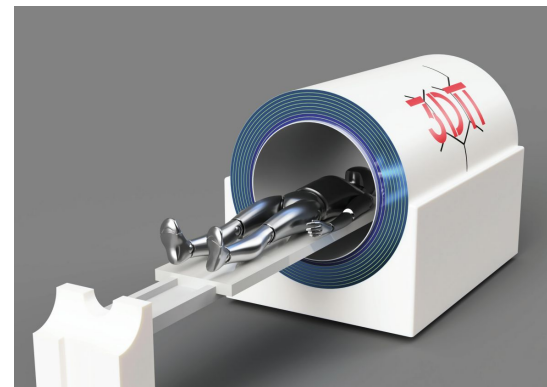
Impact of extreme ultraviolet radiation on the scintillation of pure and xenon-doped liquid argon

LIDINE 2025 Hong Kong

Evangelia Nikoloudaki on behalf of the [X-ArT collaboration](#)

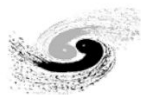
Xenon doped liquid argon

- **faster** scintillation: sub-nanosecond timing resolution
- **higher** photon and ionization yield
- **longer** photon attenuation length
- lower energy **thresholds**
- cost effective
- argon boiling **temperature**



X-ArT: Xenon-Argon Technology

1. Study the **thermodynamic** properties :
 - a. Ar-Xe **phase diagram**
 - b. Maximum Xe **solubility** in LAr
2. Characterize the **Ar-Xe response** in scintillation and ionization up to the maximum Xe solubility
 - a. phase 1: **scintillation** only up to 40 ppm of xenon concentration
 - b. phase 2: **ionization** up to maximum solubility



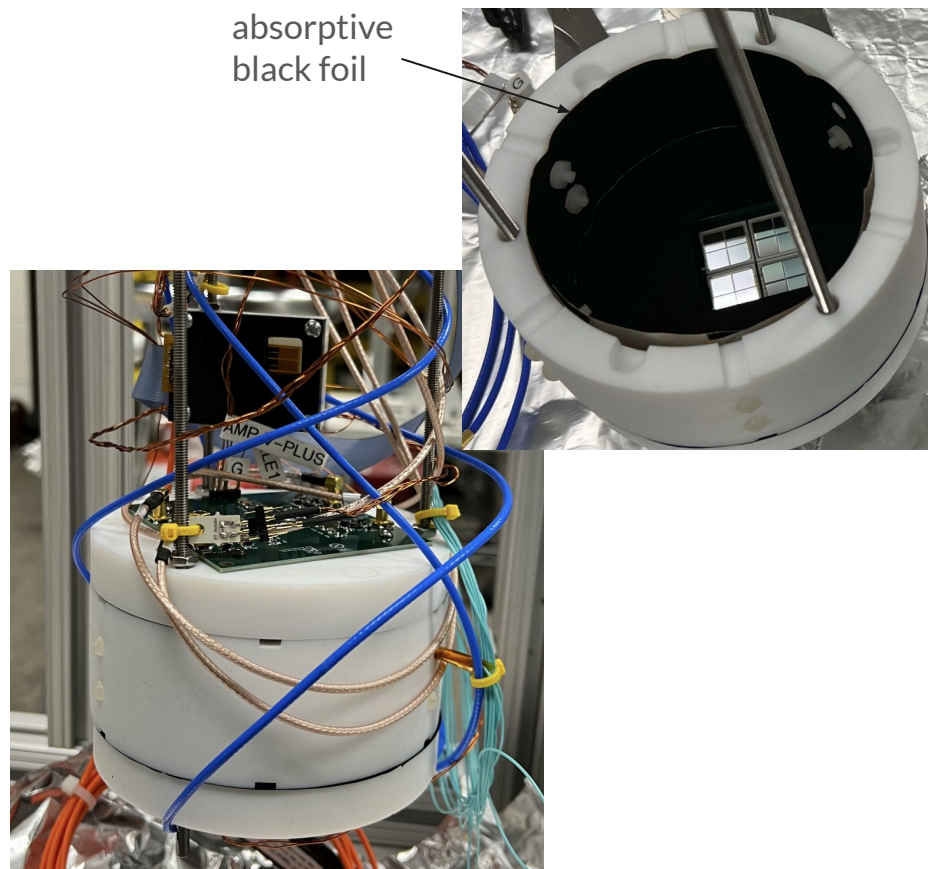
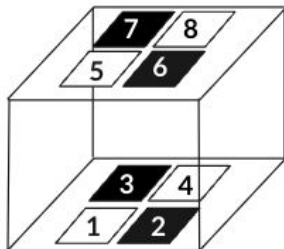
Institute of High Energy Physics
Chinese Academy of Sciences

ASTROCENT



Single phase LAr cylindrical chamber

- 4.5 cm height / 9.5 cm diameter
- **no TPB** wavelength shifter
- **black foil** to prevent reflections
- 32 VUV-sensitive Hamamatsu S13371 SiPMs
 - 4 SiPMs per channel (8 channels)
 - 4 channels **with quartz window (WW)**
 - 4 channels **without window (WL)**



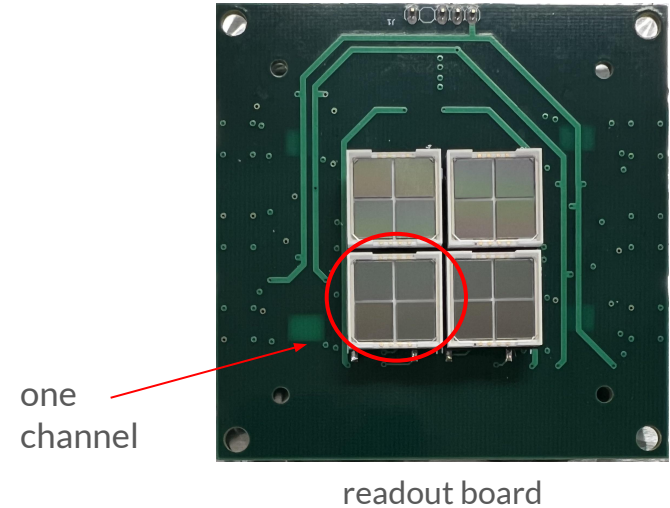
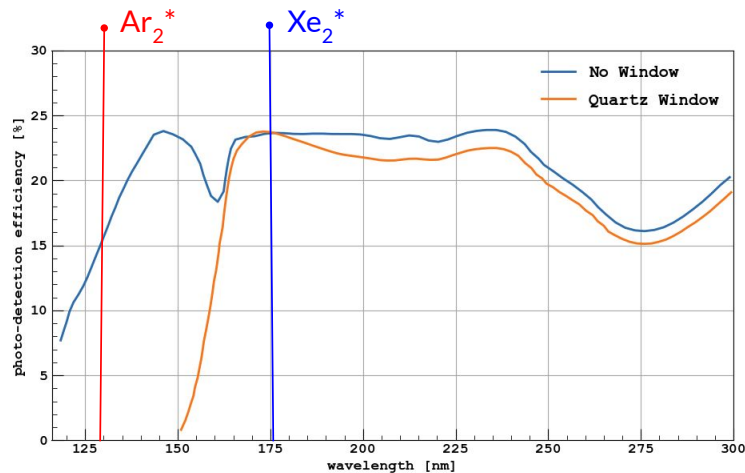
Detection channels

WW channels: sensitive above ~ 150 nm

→ detect **only** Xe_2^* photons (175 nm)

WL channels: sensitive above ~ 60 nm

→ detect **both** Xe_2^* (175 nm) **and** Ar_2^* (128 nm) photons

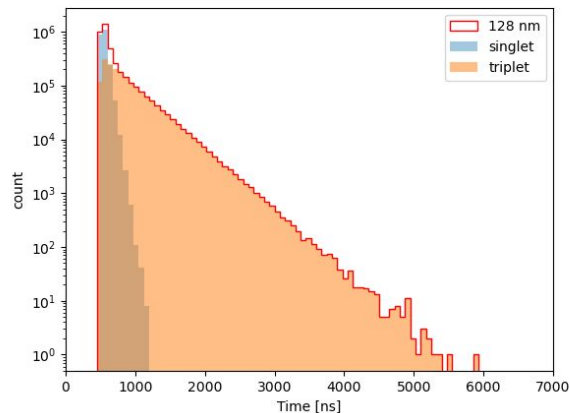


Characterization of the LAr response

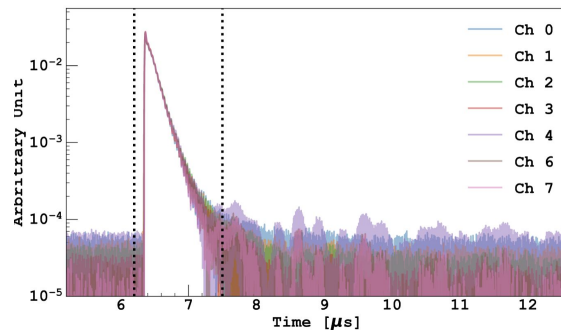
Pure LAr measurement (WL-SiPMs only) to constrain the Ar_2^* **triplet lifetime** and characterize the **LAr purity**.

LAr scintillation response model:

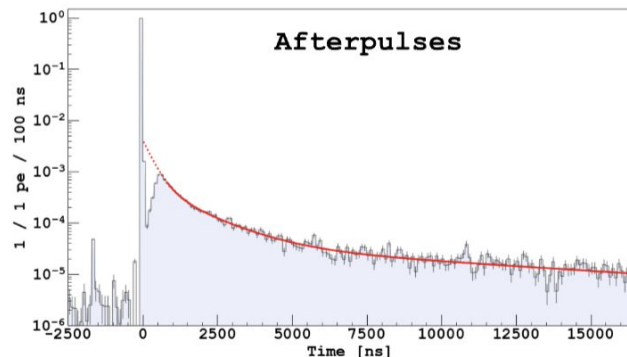
sum of singlet and triplet state exponentials $\otimes$ SiPM time response $\otimes$ SiPM AP time profile



Ar_2^* excited states:
singlet (6 ns)
triplet (1600 ns)



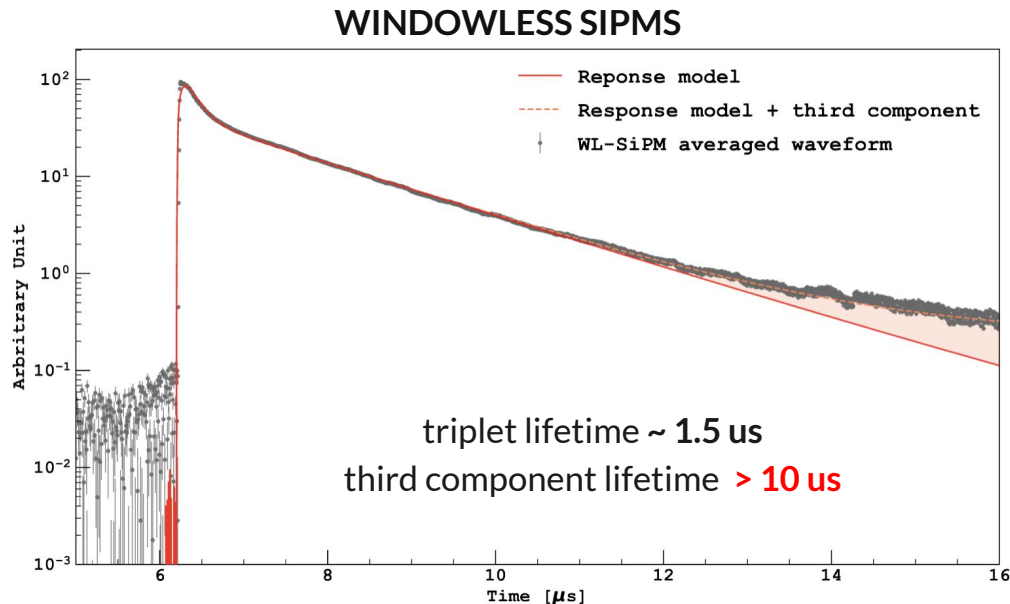
from laser calibrations



three exponential model

Characterization of the LAr response

Long component observed with WL-SiPMs:



In literature it is assigned to:

- TPB fluorescence
- Teflon fluorescence
- Near-infrared photons (> 800 nm)

TPB fluorescence ? $\rightarrow$ NO

- no TBP in the X-ArT setup

Teflon fluorescence ? $\rightarrow$ NO

- all teflon components covered with black foil

Near-infrared photons ? $\rightarrow$ NO

- detected at < 150 nm

Afterpulses ? $\rightarrow$ NO

- APs only cannot explain the long tail

EUV emission in LAr

Ar-I: neutral argon (Ar^*)

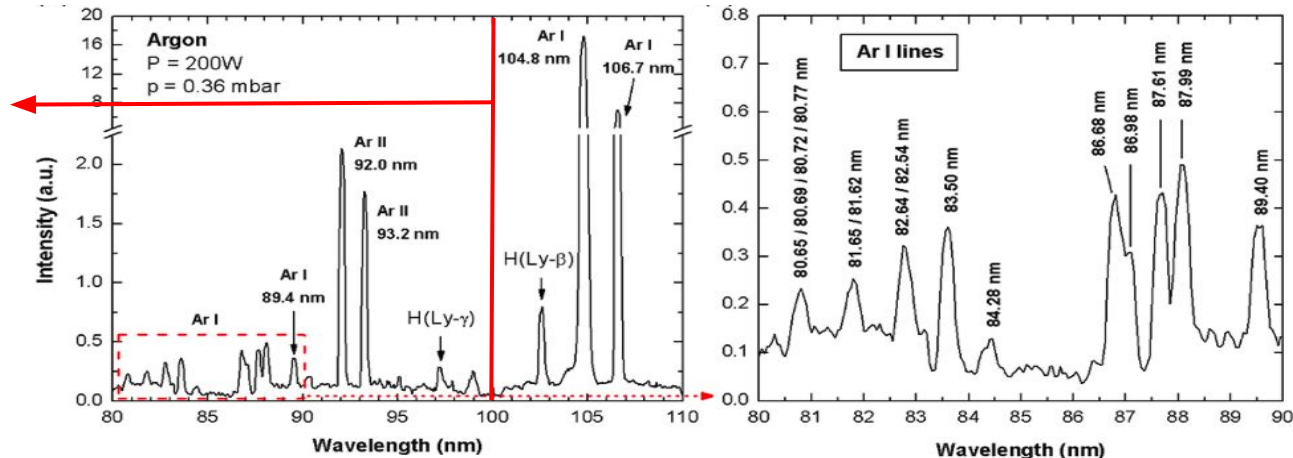
Ar-II: singly or multiple ionized argon (Ar^{q+})

EUV range: $\sim 10\text{-}100\text{ nm}$

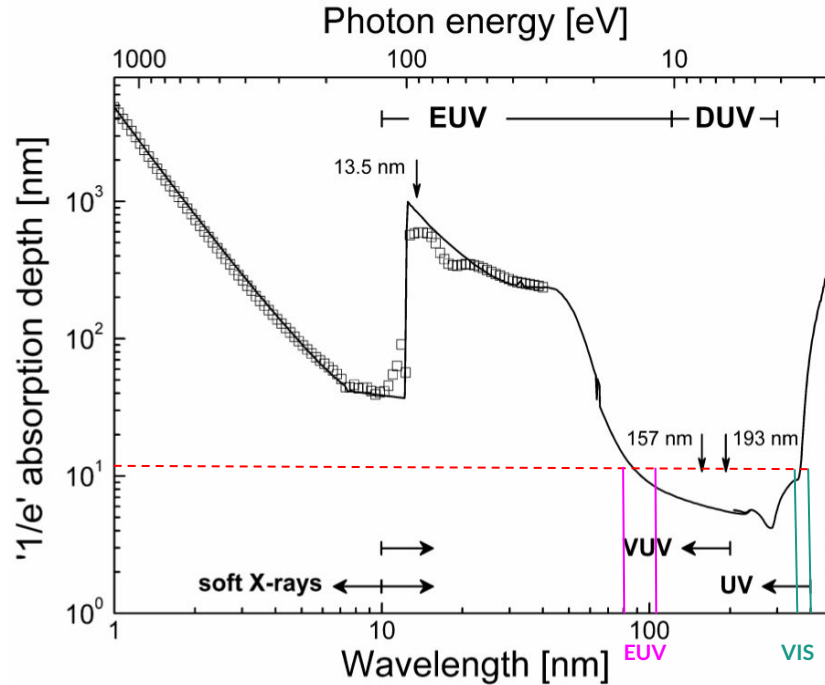
Emission from metastable states: **ms to s**

1. It is well known from atomic physics that Ar-I and Ar-II emit EUV photons from metastable levels.
2. EUV photons with wavelength $< 100\text{ nm}$ or energy $> 12.1\text{ eV}$ can ionize Xe atoms.

**Xe
ionization
threshold**



EUV detectable with SiPMs? → YES



**EUV and VIS
have almost the
same absorption
length in silicon.**

Fig. 7. $1/e'$ absorption depth in Si as a function of incident radiation wavelength (Palik, 1985; Henke data).

EUV detectable with TPB/PMTs? → YES

Eur. Phys. J. C (2018) 78:329

TPB is efficient at EUV.

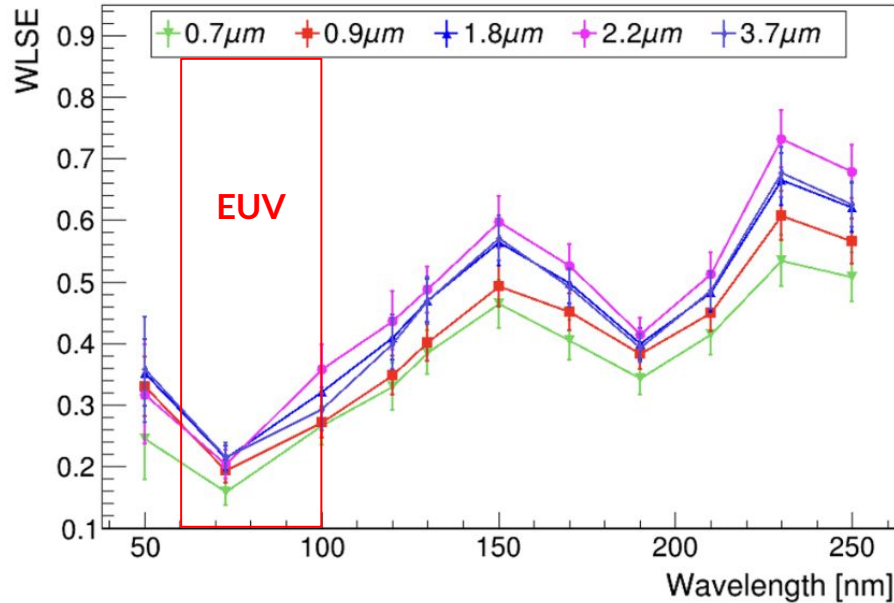
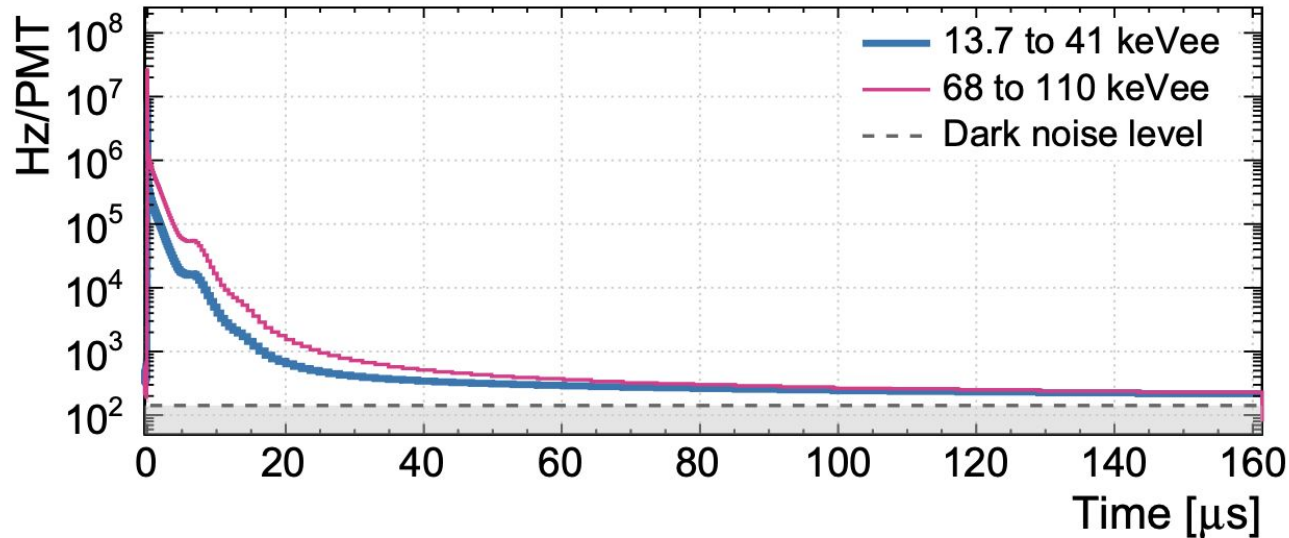


Fig. 16 Absolute WLSE efficiency for several samples of various thickness

Long component in DEAP-3600

DEAP-3600:

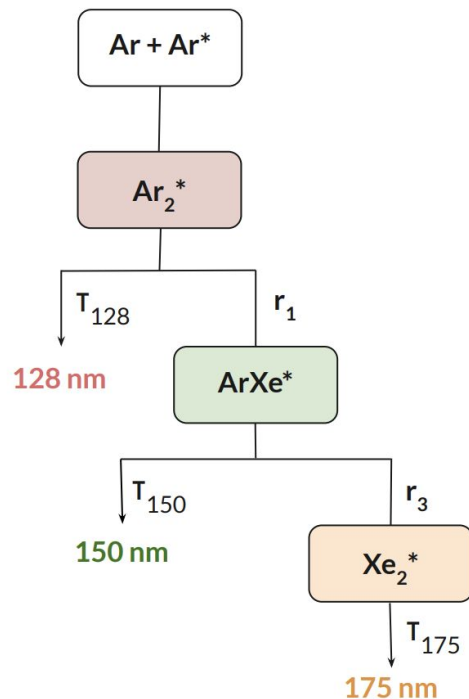
- **liquid argon** detector for dark matter searches
- uses **TPB** wavelength shifter (UV to VIS conversion) and **PMTs** to detect the scintillation light



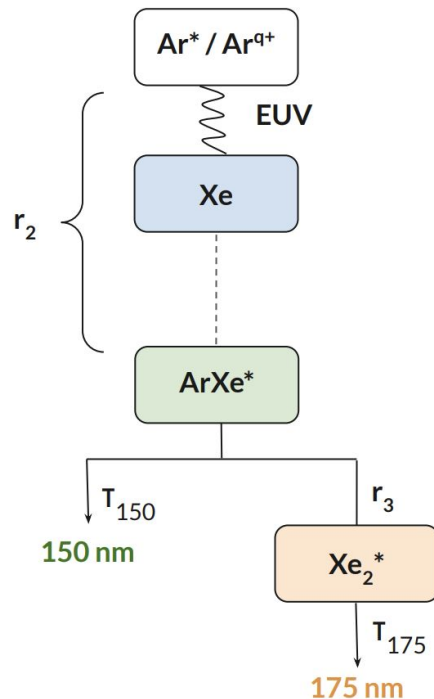
The Xe-Ar scintillation model

NEW COMPONENT

Collisional Branch



Radiative Branch



$r_1 \rightarrow$ rate of ArXe^* formation

$r_2 \rightarrow$ rate of **EUV-induced** ionization and subsequent ArXe^* formation

$r_3 \rightarrow$ rate of Xe_2^* formation

Two competitions between:

- triplet decay and ArXe^* formation
- ArXe^* de-excitation and Xe_2^* formation

The analytical model

WW-SiPMs

WL-SiPMs

collisional

128 nm

$$A \cdot \left[f_p \cdot \frac{e^{-\frac{t}{\tau_s}}}{\tau_s} + (1 - f_p) \cdot \frac{e^{-k_1 t}}{1/k_1} \right]$$

150 nm/175 nm

$$B_1 \cdot \frac{k_1 k_3}{k_1 - k_3} \cdot [e^{-k_3 t} \cdot (1 - e^{-(k_1 - k_3)t})]$$

175 nm

$$B_2 \cdot \frac{k_1 k_3}{k_1 - k_3} \cdot [e^{-k_3 t} \cdot (1 - e^{-(k_1 - k_3)t})]$$

radiative

150 nm/175 nm

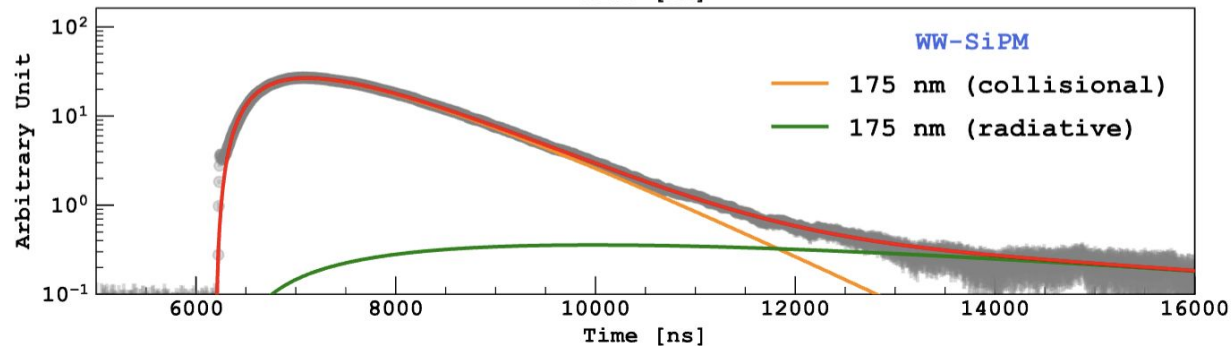
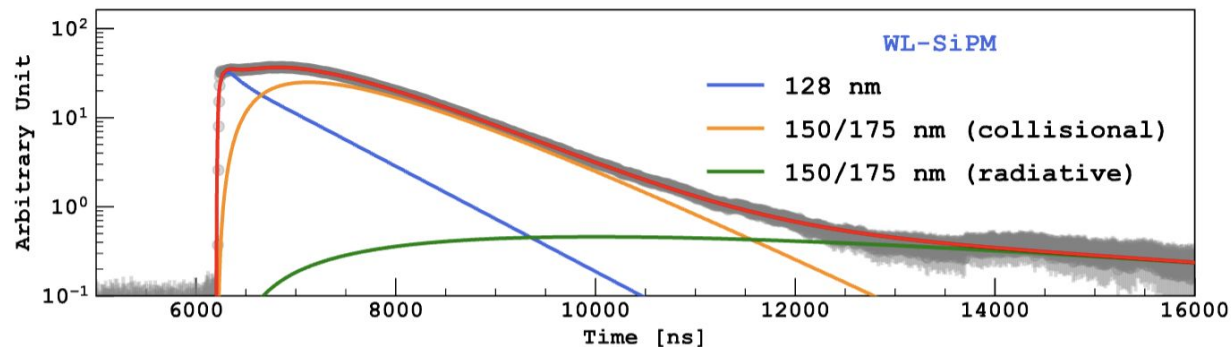
$$C_1 \cdot \frac{r_2 k_3}{r_2 - k_3} \cdot [e^{-k_3 t} \cdot (1 - e^{-(r_2 - k_3)t})]$$

175 nm

$$C_2 \cdot \frac{r_2 k_3}{r_2 - k_3} \cdot [e^{-k_3 t} \cdot (1 - e^{-(r_2 - k_3)t})]$$

Simultaneous fit of WL- and WW-SiPM waveforms

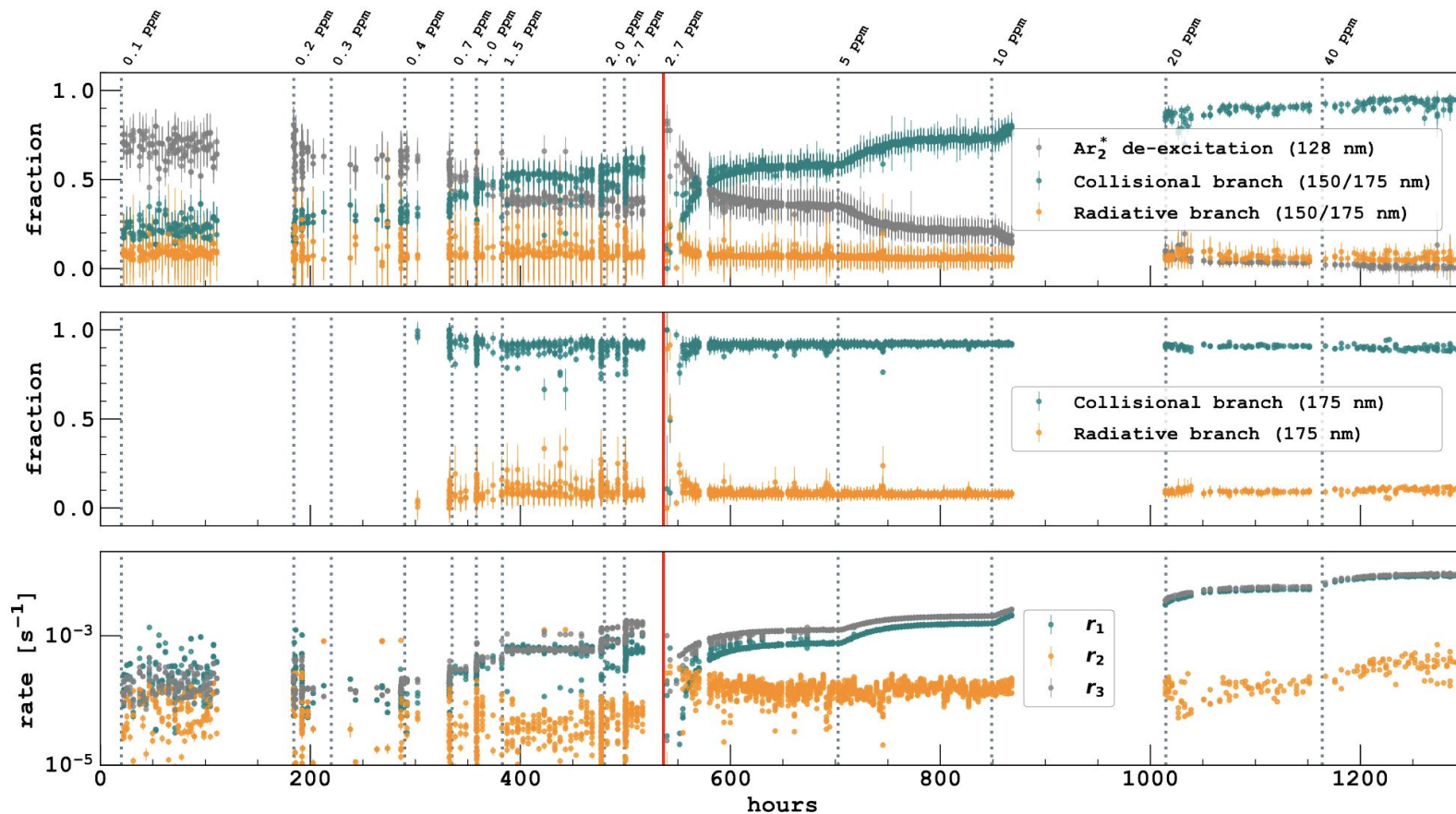
2.7 ppm of Xe and ^{60}Co source



rate parameters (r_1 , r_2 , and r_3) are constrained between the two fits

- Non-zero contribution from the radiative process.
- The collisional process alone, cannot explain the data.

Effects of the Xe concentration



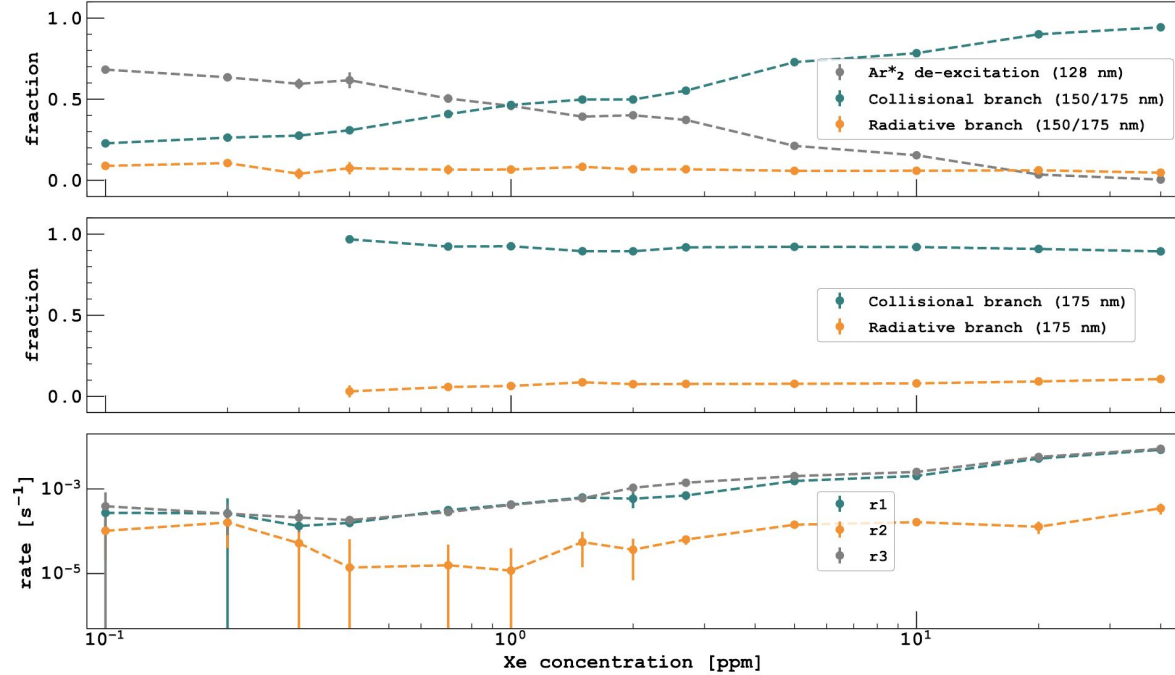
Effects of the Xe concentration

Collisional branch increase with Xe:

- increasing probability of collisional energy transfer

Radiative branch is constant:

- depends on atomic Ar excitation
- mean EUV - Xe scattering length is negligible with respect to the chamber size

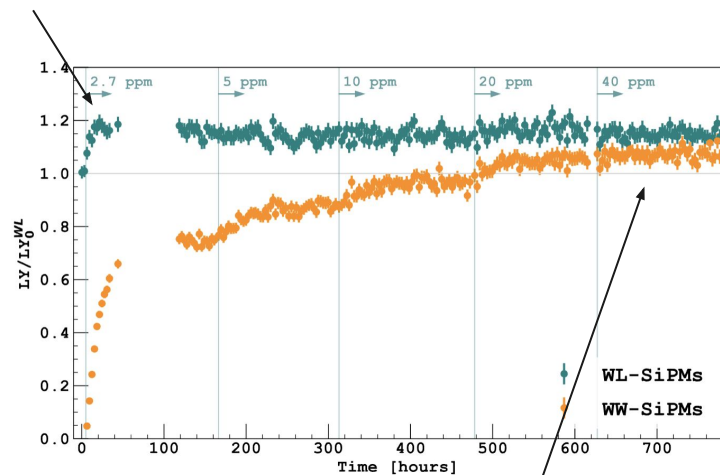


Xe-doped liquid argon light yield and PSD

LY increases with increasing Xe concentration.

overall LY = sum of Ar_2^* , Xe_2^* and ArXe^* photons

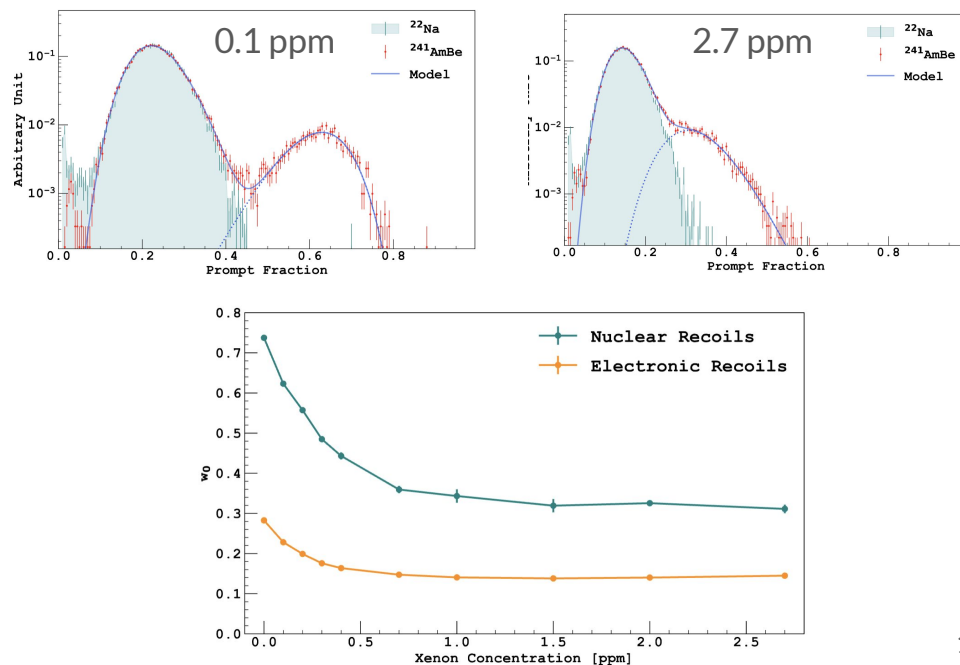
increase due to the radiative component



128 nm becomes negligible

PSD degrades with increasing Xe concentration.

PSD observable w: the fraction of light in the first 300 ns



EUV as natural source of spurious electrons

Spurious electrons:

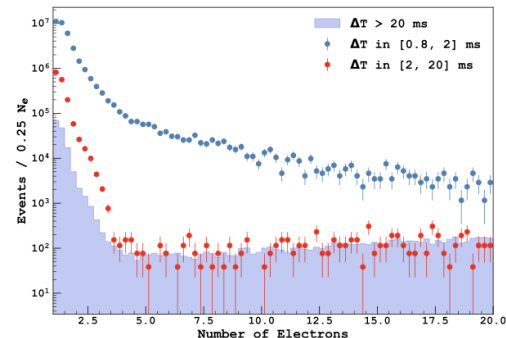
Electroluminescence pulses of unknown origin equivalent to one or few electrons, **correlated** (ms scale) with **preceding events** in the TPC and with **impurities**.

EUV can photo-ionize Xe as well as impurities,

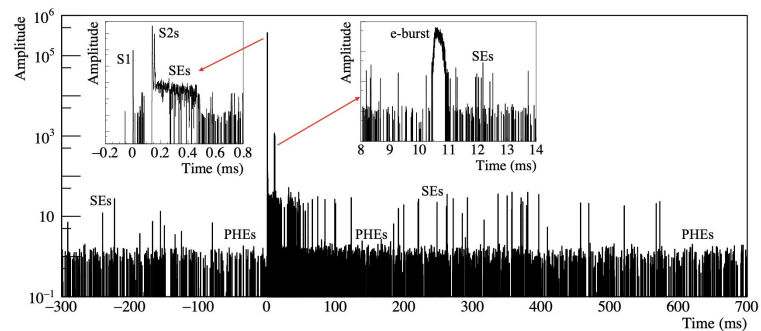
for instance: O_2 (12.1 eV), CH_4 (12.6 eV) and Kr (14.0 eV)

- correlation with preceding events exciting atomic Ar states
- time delays dominated by metastable atomic Ar states

LAr:



LXe:

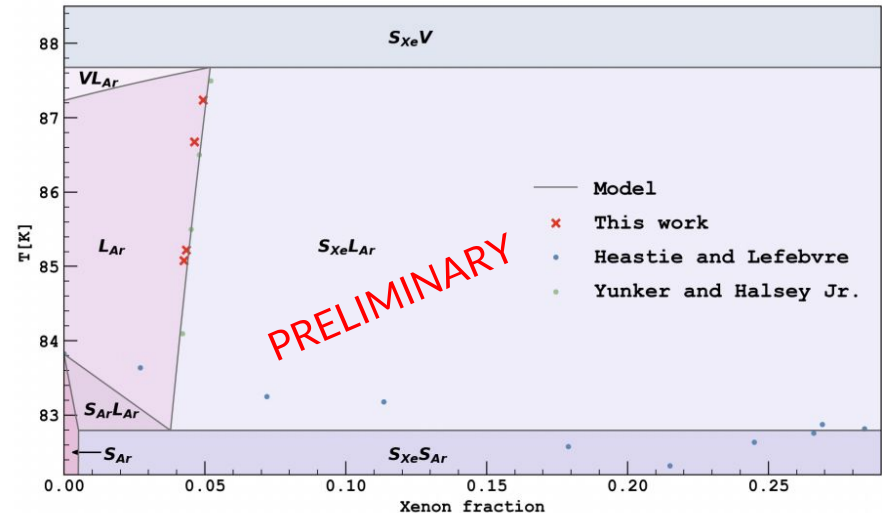
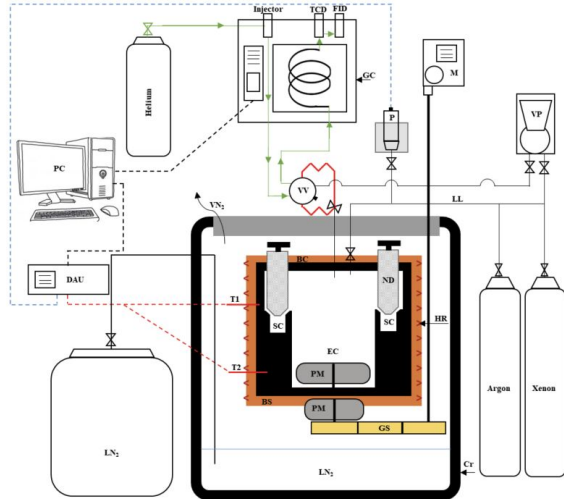


Bonus: first phase-diagram

Study of the solid-vapor and solid-liquid phase equilibrium in the 85-150 K temperature range.

Observations:

1. decrease of xenon solubility in the vapor phase with decreasing temperature
2. higher but decreasing solubility of xenon in the liquid phase with decreasing temperature: maximum at **4.2%**
3. measurements in very good agreement with model expectations



Conclusions

1. The **radiative component** addition models pure and xenon-doped liquid argon scintillation.
2. In the xenon-doped system we observed an increase in **LY** up to 15 % and a degradation in **PSD** with increasing Xe concentration.
3. EUV photon emission can explain the **spurious electrons** in pure LAr, through photoionization of impurities.
4. Maximum solubility and phase diagram of the xenon-argon mixture was measured.

Next steps:

- ❑ new campaign for investigation of the long component of LAr scintillation
- ❑ characterization of the ionization response of Xe doped LAr
- ❑ thermodynamics paper by the end of the year.



Backup

Argon and xenon as scintillators

Ar

+

+

+

+

scalability
radio purity: UAr
excellent PSD
low dark count rate SiPM

—

—

—

not directly detectable wavelength
long scintillation times
short attenuation length

Xe

+

+

+

+

higher WIMP cross section
spin-dependent sensitivity
fast response
directly detectable wavelength

—

—

—

expensive and limited
higher dark count rate SiPM
poor PSD

SiPM specifications

WW-SiPMs

■ Electrical and optical characteristics

(Typ. T = 25 deg C, Vr = Vop unless otherwise noted)

Parameters	Symbol	Value (typ.)	Unit
Spectral response range	λ	155 to 900	nm
Peak sensitivity wavelength	λ_p	500	nm
Photon detection efficiency at λ_p *2	-	32	%
Photon detection efficiency at 175nm (in vacuum) *2	-	24	%
Breakdown voltage	V _{br}	53 +/- 5	V
Recommended operating voltage *3	V _{op}	V _{br} + 4.0	V
Dark count rate / channel	DCR	4.0 (MAX:12)	Mcps
Crosstalk probability	P _{CT}	3	%
Terminal capacitance at Vop / channel	C _t	1200	pF
Gain	M	2.55×10^6	-
Temperature coefficient of reverse voltage Around room temperature	ΔTV_{op}	54	mV/deg C

*2 : Photon detection efficiency does not include crosstalk and after pulse.

*3 : Refer to the data attached for each products.

WL-SiPMs

■ Electrical and optical characteristics

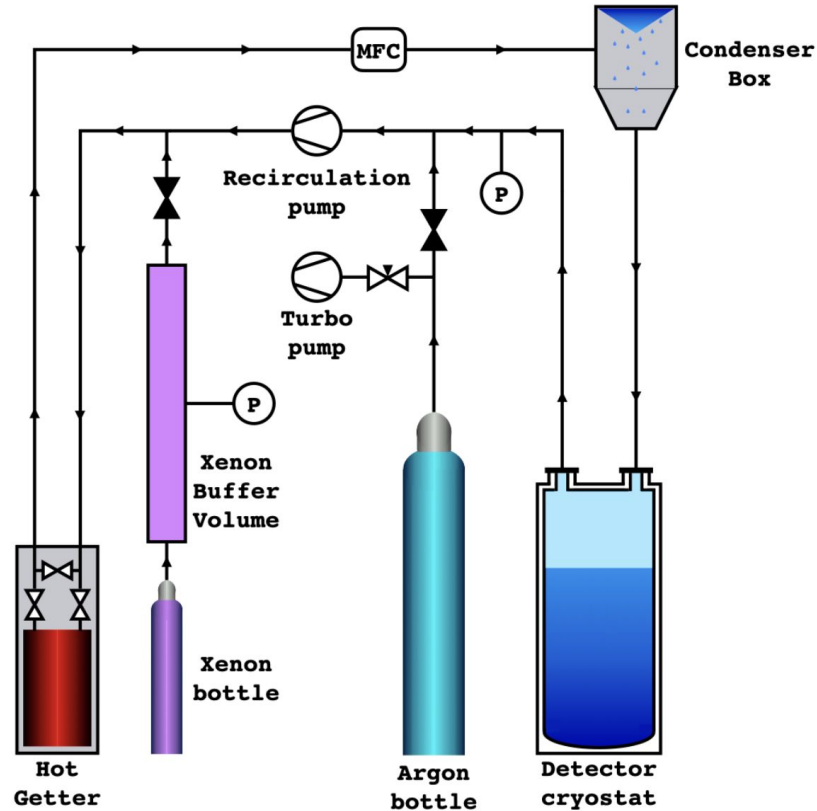
(Typ. T = 25 deg C, Vr = Vop unless otherwise noted)

Parameters	Symbol	Value (typ.)	Unit
Spectral response range	λ	120 to 900	nm
Peak sensitivity wavelength	λ_p	500	nm
Photon detection efficiency at λ_p *2	-	32	%
Photon detection efficiency at 175nm (in vacuum) *2	-	24	%
Breakdown voltage	V _{br}	53 +/- 5	V
Recommended operating voltage *3	V _{op}	V _{br} + 4.0	V
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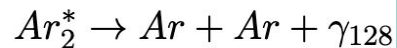
Custom-designed cryogenic system at Princeton



Xe-doped liquid argon scintillation

We fit the waveforms of WW and WL channels simultaneously to disentangle the contributions of components with different wavelengths.

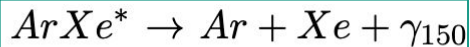
1. Direct Ar scintillation:



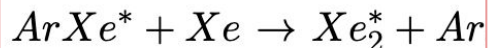
2. When Xe is added, ArXe is formed: $\text{Ar}_2^* + \text{Xe} \rightarrow \text{ArXe}^* + \text{Ar}$

At ~ 0.2 ppm of Xe:

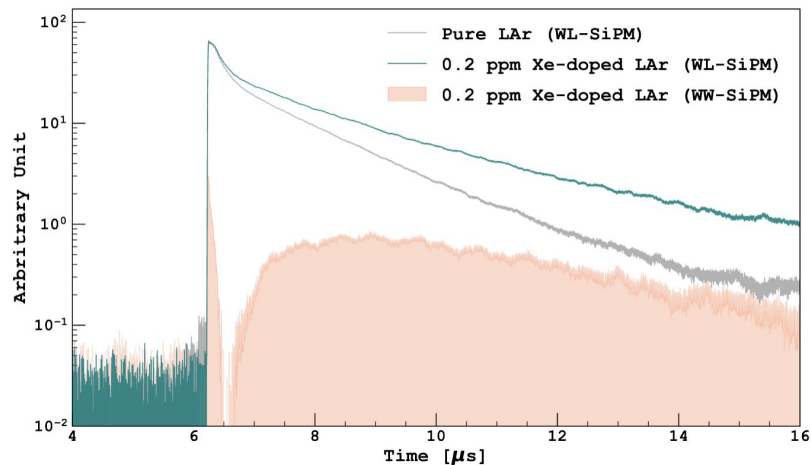
- slow component observed with WL-SiPMs with lifetime ~ 5 ms from ArXe^* de-excitation that emits 150 nm photons:



At increasing Xe concentration the Xe_2^* reaction dominates:



Xe_2^* decays emitting 175 nm light



6.3 hours after injecting 2.7 ppm of Xe

The Ar-Xe scintillation model

Probability density functions (pdfs) describing the signals observed by the WL and WW channels:

$$f_{WL}(t) = \frac{A}{\varepsilon_{128}} f_{128}(t) + \frac{B_1}{\varepsilon_{150/175}} f_c(t) + \frac{C_1}{\varepsilon_{150/175}} f_r(t)$$

$$f_{WW}(t) = \frac{B_2}{\varepsilon_{150/175}} f_c(t) + \frac{C_2}{\varepsilon_{150/175}} f_r(t)$$

(convoluted with SiPM response)

Amplitudes

A: Ar_2^* de-excitation

B1: collisional component in WL

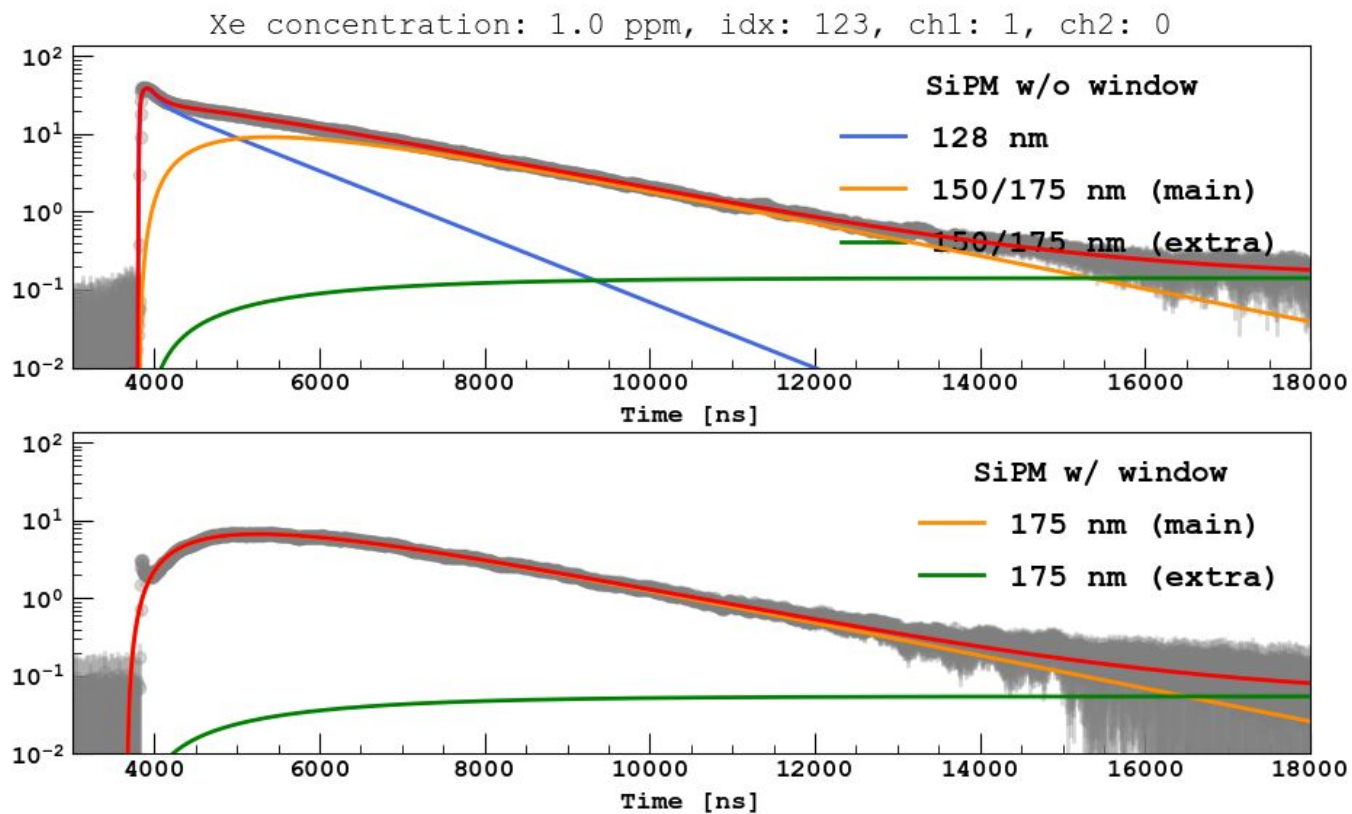
C1: radiative component in WL

B2: collisional component in WW

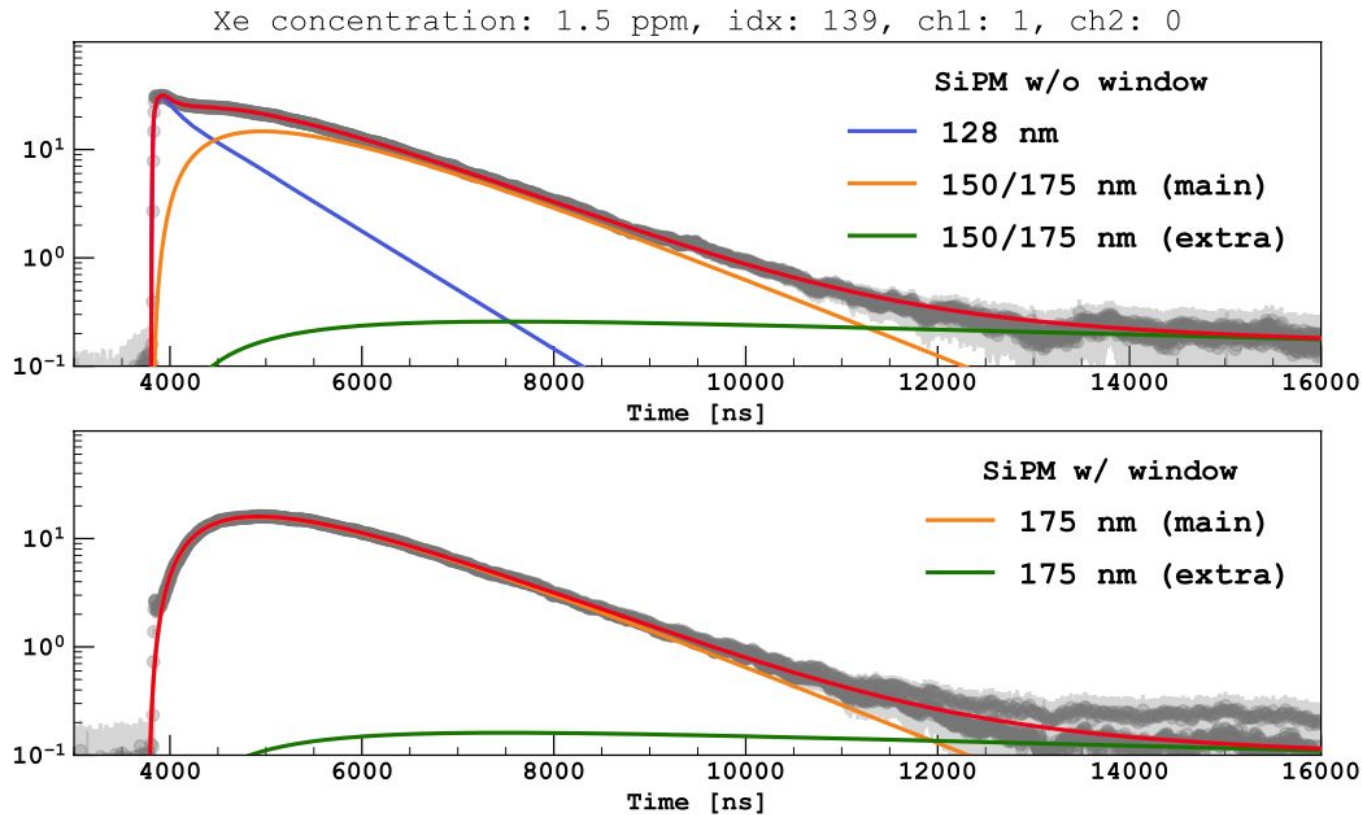
C2: radiative component in WW

ε : photodetection efficiencies at different wavelengths

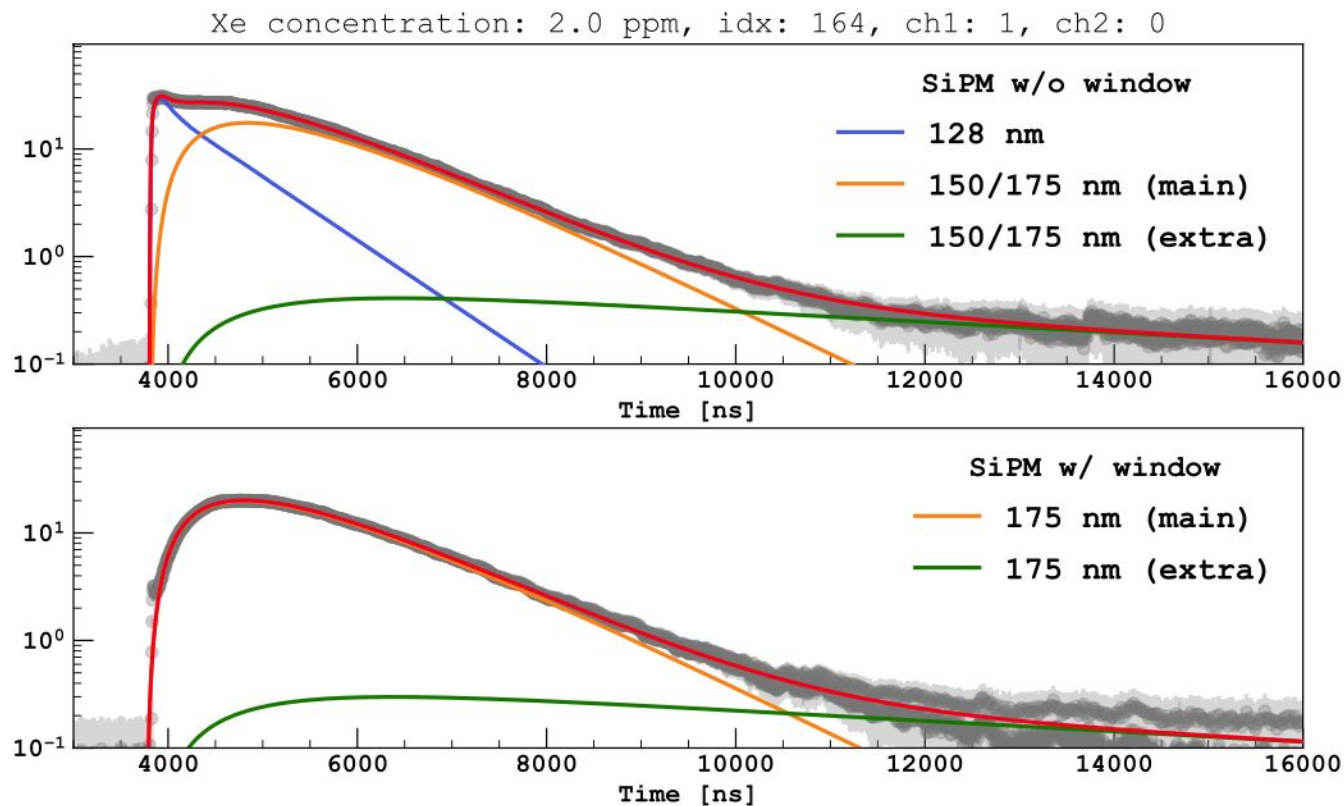
1.0 ppm



1.5 ppm



2.0 ppm



2.7 ppm

